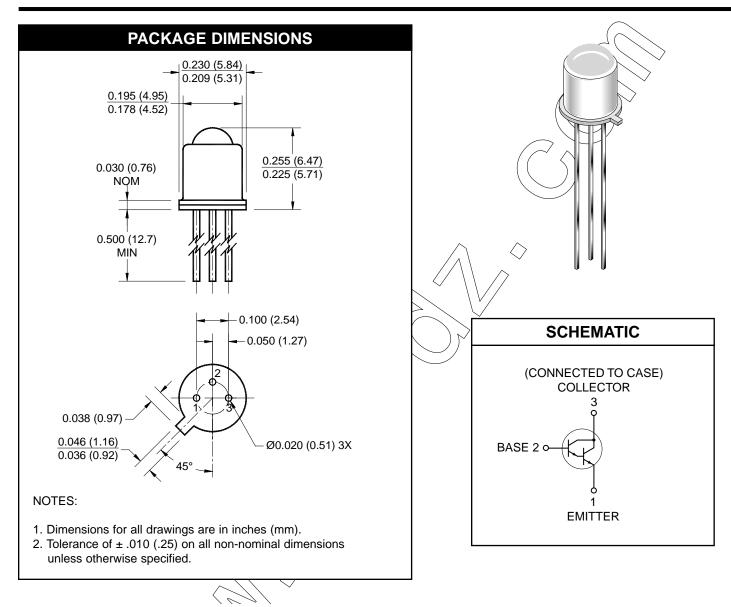
L14F1 L14F2



DESCRIPTION

The L14F1/L14F2 are silicon photodarlingtons mounted in a narrow angle, TO-18 package.

FEATURES

- · Hermetically sealed package
- · Narrow reception angle



L14F1 L14F2

Parameter	Symbol Rating		Unit	
Operating Temperature	T _{OPR}	-65 to +125	°C	
Storage Temperature	T _{STG}	-65 to +150	°C	
Soldering Temperature (Iron)(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	°C	
Soldering Temperature (Flow)(3,4 and 6)	T _{SOL-F}	260 for 10 sec	°C	
Collector to Emitter Breakdown Voltage	V _{CEO}	25	V	
Collector to Base Breakdown Voltage	V _{CBO}	25	V	
Emitter to Base Breakdwon Voltage	V _{EBO}	12	V	
Power Dissipation (T _A = 25°C) ⁽¹⁾	P _D	300	mW	
Power Dissipation (T _C = 25°C) ⁽²⁾	P _D	600	mW	

NOTE:

- 1. Derate power dissipation linearly 3.00 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 6.00 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension.
- 7. Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
- 8. Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 0.05 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 0.2 mW/cm².

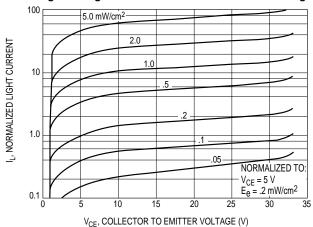
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ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS		
Collector-Emitter Breakdown	$I_{\rm C} = 10 \text{ mA}, Ee = 0$	BV _{CEO}	25		_	V		
Emitter-Base Breakdown	$I_E = 100 \mu A, Ee = 0$	BV _{EBO}	12		_	V		
Collector-Base Breakdown	$I_{C} = 100 \mu A, Ee = 0$	BV _{CBO}	25		_	V		
Collector-Emitter Leakage	V _{CE} = 12 V, Ee = 0	I _{CEO}	_		100	nA		
Reception Angle at 1/2 Sensitivity		θ		±8		Degrees		
On-State Collector Current L14F1	Ee = .125 mW/cm ² , $V_{CE} = 5 V^{(7)}$	I _{C(ON)}	7.5		_	mA		
On-State Collector Current L14F2	Ee = .125 mW/cm ² , $V_{CE} = 5 V^{(7)}$	I _{C(ON)}	2.5			mA		
Rise Time	I_C = 10 mA, V_{CC} = 5 V, R_L =100 Ω	t _r		300		μs		
Fall Time	I_C = 10 mA, V_{CC} = 5 V, R_L =100 Ω	t _f		250		μs		



L14F1 L14F2

Figure 1. Light Current vs. Collector to Emitter Voltage



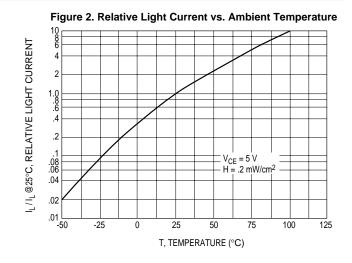
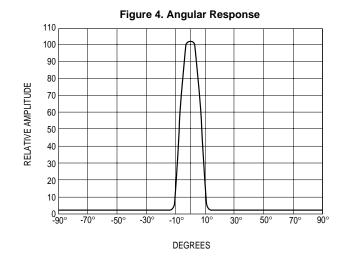


Figure 3. Spectral Response 1.0 0.9 RELATIVE SPECTRAL RESPONSE 0.8 0.7 0.6 0.4 0.3 0.1 0 400 500 600 700 800 900 1000 1100

 λ , WAVE LENGTH (NANOMETERS)



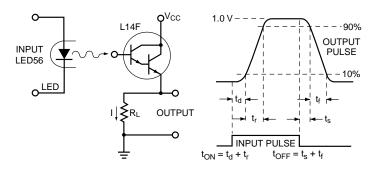
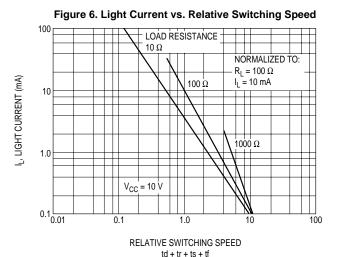


Figure 5. Test Circuit and Voltage Waveforms



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